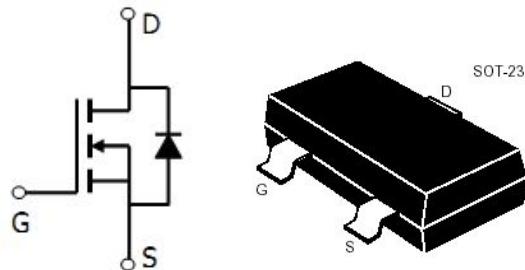


**GM2100**
**SOT-23 場效應晶體管(SOT-23 Field Effect Transistors)**


### N-Channel Enhancement-Mode MOS FETs

**N 沟道增强型 MOS 场效应管**

### ■MAXIMUM RATINGS 最大額定值

Characteristic 特性參數	Symbol 符號	Max 最大值	Unit 單位
Drain-Source Voltage 漏極-源極電壓	$BV_{DSS}$	20	V
Gate- Source Voltage 柵極-源極電壓	$V_{GS}$	$\pm 10$	V
Drain Current (continuous) 漏極電流-連續	$I_D$	10	A
Drain Current (pulsed) 漏極電流-脉冲	$I_{DM}$	20	A
Total Device Dissipation 總耗散功率	$P_D$	1400	mW
TA=25°C 環境溫度為 25°C			
Junction 結溫	$T_J$	150	°C
Solder Temperature/Solder Time 焊接溫度/焊接時間	T/t	260/10	°C/S
Storage Temperature 儲存溫度	$T_{stg}$	-55 to +150	°C

### ■DEVICE MARKING 打標

**GM2100=2100**



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**GM2100**

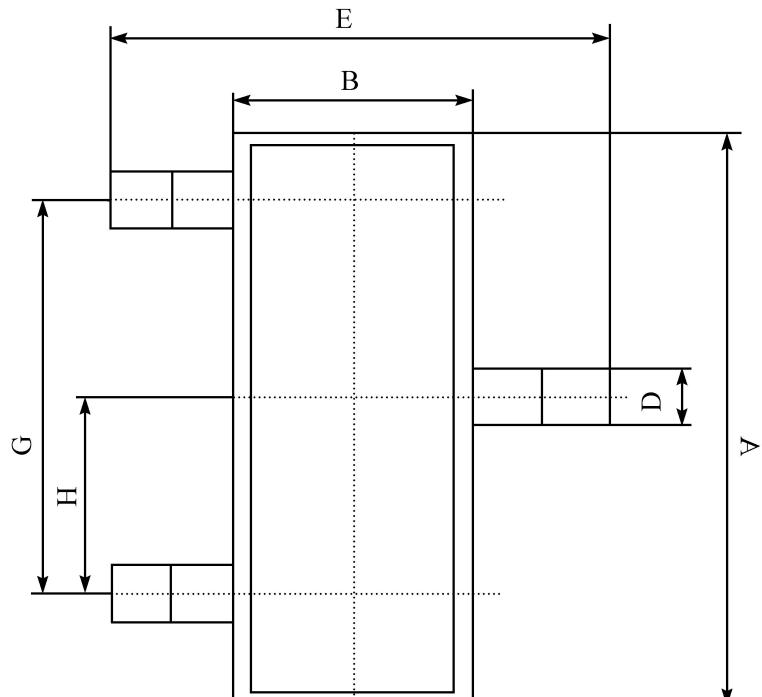
GM2100

## ■ELECTRICAL CHARACTERISTICS 電特性

( $T_A=25^\circ\text{C}$  unless otherwise noted 如無特殊說明，溫度為  $25^\circ\text{C}$ )

Characteristic 特性參數	Symbol 符號	Min 最小值	Typ 典型值	Max 最大值	Unit 單位
Drain-Source Breakdown Voltage 漏極-源極擊穿電壓( $I_D = 250\mu\text{A}$ , $V_{GS}=0\text{V}$ )	$\text{BV}_{DSS}$	20	—	—	V
Gate Threshold Voltage 柵極開啓電壓( $I_D = 250\mu\text{A}$ , $V_{GS} = V_{DS}$ )	$V_{GS(\text{th})}$	0.5	—	1.0	V
Diode Forward Voltage Drop 內附二極管正向壓降( $I_S=1\text{A}$ , $V_{GS}=0\text{V}$ )	$V_{SD}$	—	—	1.5	V
Zero Gate Voltage Drain Current 零柵壓漏極電流( $V_{GS}=0\text{V}$ , $V_{DS}=16\text{V}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Gate Body Leakage 柵極漏電流( $V_{GS}=\pm 10\text{V}$ , $V_{DS}=0\text{V}$ )	$I_{GSS}$	—	—	$\pm 100$	nA
Static Drain-Source On-State Resistance 静态漏源導通電阻( $I_D = 6\text{A}$ , $V_{GS} = 4.5\text{V}$ )	$R_{DS(\text{ON})}$	—	10	12	$\text{m}\Omega$
Static Drain-Source On-State Resistance 静态漏源導通電阻( $I_D = 4.5\text{A}$ , $V_{GS} = 2.5\text{V}$ )	$R_{DS(\text{ON})}$	—	12	16	$\text{m}\Omega$
Input Capacitance 輸入電容 ( $V_{GS}=0\text{V}$ , $V_{DS}= 10\text{V}$ , $f=1\text{MHz}$ )	$C_{ISS}$	—	600	—	pF
Output Capacitance 輸出電容 ( $V_{GS}=0\text{V}$ , $V_{DS}= 10\text{V}$ , $f=1\text{MHz}$ )	$C_{OSS}$	—	120	—	pF
Turn-ON Time 开啓時間 ( $V_{DS}= 10\text{V}$ , $I_D = 3\text{A}$ , $R_{GEN}=6\Omega$ )	$t_{(\text{on})}$	—	8	—	ns
Turn-OFF Time 關斷時間 ( $V_{DS}= 10\text{V}$ , $I_D = 3\text{A}$ , $R_{GEN}=6\Omega$ )	$t_{(\text{off})}$	—	60	—	ns

Pulse Width  $\leq 300 \mu\text{s}$ ; Duty Cycle  $\leq 2.0\%$

**GM2100**
**■DIMENSION 外形封裝尺寸**
**單位(UNIT): mm**


序號	數值及公差
A	$2.90 \pm 0.10$
B	$1.30 \pm 0.10$
C	$1.00 \pm 0.10$
D	$0.40 \pm 0.10$
E	$2.40 \pm 0.20$
G	$1.90 \pm 0.10$
H	$0.95 \pm 0.05$
J	$0.13 \pm 0.05$
K	$0.00-0.10$
M	$\geq 0.2$
N	$0.60 \pm 0.10$
P	$7 \pm 2^\circ$

